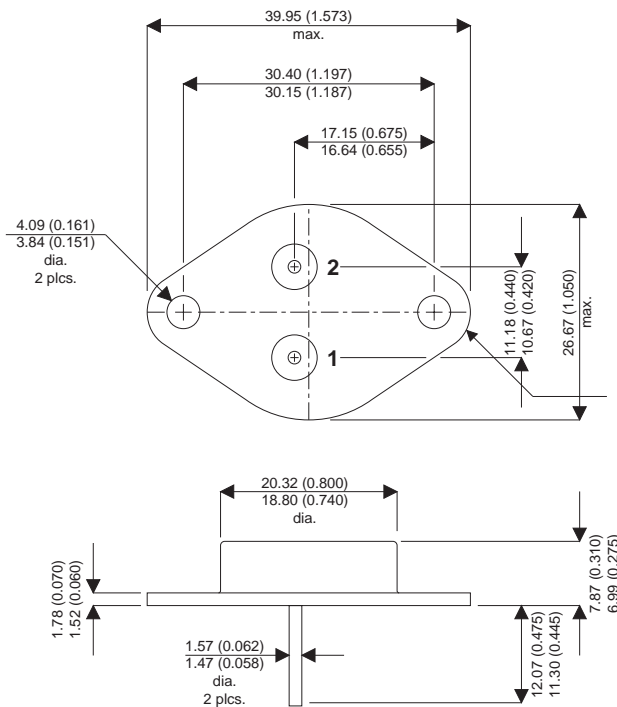


MECHANICAL DATA

Dimensions in mm (inches)



TO-3 Metal Package

Pin 1 – Gate Pin 2 – Source Case – Drain

**N-CHANNEL
POWER MOSFET**

V_{DSS} **200V**
 $I_{D(cont)}$ **30A**
 $R_{DS(on)}$ **0.085Ω**

FEATURES

- HERMETICALLY SEALED TO-3 METAL PACKAGE
- SIMPLE DRIVE REQUIREMENTS
- SCREENING OPTIONS AVAILABLE

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 25^{\circ}C$)	30A
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 100^{\circ}C$)	19A
I_{DM}	Pulsed Drain Current ¹	120A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	150W
	Linear Derating Factor	1.2W/°C
E_{AS}	Single Pulse Avalanche Energy ²	200mJ
I_{AR}	Avalanche Current ²	30A
E_{AR}	Repetitive Avalanche Energy ²	15mJ
dv/dt	Peak Diode Recovery ³	5V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150°C
T_L	Lead Temperature 1.6mm (0.63") from case for 10 sec.	300°C

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu s$, $\delta \leq 2\%$.
- 2) @ $V_{DD} = 50V, L \geq 330mH, R_G = 25\Omega$, Peak $I_L = 30A$, Starting $T_J = 25^{\circ}C$.
- 3) @ $I_{SD} \leq 30A, di/dt \leq 190A/\mu s, V_{DD} \leq BV_{DSS}, T_J \leq 150^{\circ}C$, Suggested $R_G = 2.35\Omega$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0$ $I_D = 1mA$	200		V
$\Delta BV_{DSS} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	Reference to $25^{\circ}C$ $I_D = 1mA$		0.029	$V/^{\circ}C$
$R_{DS(on)}$	Static Drain – Source On-State Resistance ¹	$V_{GS} = 10V$ $I_D = 19A$ $V_{GS} = 10V$ $I_D = 30A$		0.085 0.090	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250mA$	2	4	V
g_{fs}	Forward Transconductance ¹	$V_{DS} > 15V$ $I_D = 19A$	9		S (\bar{v})
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0$ $V_{DS} = 0.8BV_{DSS}$ $T_J = 125^{\circ}C$		25 250	μA
I_{GSS}	Forward Gate – Source Leakage	$V_{GS} = 20V$		100	nA
I_{GSS}	Reverse Gate – Source Leakage	$V_{GS} = -20V$		-100	nA
DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	$V_{GS} = 0$		3500	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		700	
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		110	
Q_g	Total Gate Charge	$V_{GS} = 10V$	55	115	nC
Q_{gs}	Gate – Source Charge	$I_D = 30A$	8	22	
Q_{gd}	Gate – Drain (“Miller”) Charge	$V_{DS} = 0.5BV_{DSS}$	30	60	
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 100V$ $I_D = 30A$ $R_G = 2.35\Omega$		35	ns
t_r	Rise Time			190	
$t_{d(off)}$	Turn–Off Delay Time			170	
t_f	Fall Time			130	
SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current			30	A
I_{SM}	Pulse Source Current ²			120	
V_{SD}	Diode Forward Voltage ¹	$I_S = 30A$ $T_J = 25^{\circ}C$ $V_{GS} = 0$		1.9	V
t_{rr}	Reverse Recovery Time	$I_F = 30A$ $T_J = 25^{\circ}C$		950	ns
Q_{rr}	Reverse Recovery Charge ¹	$d_i / d_t \leq 100A/\mu s$ $V_{DD} \leq 50V$		9.0	μC
t_{on}	Forward Turn–On Time		Negligible		
PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (measured from 6mm down drain lead to centre of die)		5.0		nH
L_S	Internal Source Inductance (from 6mm down source lead to source bond pad)		13		
THERMAL CHARACTERISTICS					
$R_{\theta JC}$	Thermal Resistance Junction – Case			0.83	$^{\circ}C/W$
$R_{\theta CS}$	Thermal Resistance Case – Sink		0.12		
$R_{\theta JA}$	Thermal Resistance Junction – Ambient			30	

Notes

- 1) Pulse Test: Pulse Width $\leq 300ms$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.

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